


REMARKS

Claims 1-19 and 41-47 are canceled, leaving claims 20-40 pending in the application. Applicant requests substantive examination of pending claims 20-40.

Respectfully submitted,

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

priority Application Serial No. 09/633,556
priority Filing Date August 7, 2000
Inventor Gurtej S. Sandhu et al.
Assignee Micron Technology, Inc.
priority Group Art Unit 2813
priority Examiner Laura M. Schillinger
Attorney's Docket No. MI22-1897
Title: Methods of Forming Transistors

**VERSION WITH MARKINGS TO SHOW CHANGES MADE
ACCOMPANYING PRELIMINARY AMENDMENT**

In the Specification

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The title is amended as follows: ~~Transistor Structures, Methods of
Incorporating Nitrogen into Silicon Oxide-Containing Layers; and Methods of
Forming Transistors~~

The following is inserted on p. 1 before the "Technical Field" section,

CROSS REFERENCE TO RELATED APPLICATION

This patent resulted from a divisional application of U.S. Patent Application
Serial No. 09/633,556, which was filed on August 7, 2000.

In the Claims

Claims 1-19 and 41-47 are canceled.

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